Listing of Claims

This listing of claims replaces all prior versions, and listings, of claims in the application:

Claims 1-19. (Canceled)

(New) A lithography method comprising: 20.

placing a pellicle comprising polyvinylidene fluoride (PVDF) on a side of a lithography mask; and

transmitting an electromagnetic radiation through the pellicle to form a lithographic image on a substrate.

- (New) The method of claim 20, wherein placing the 21. pellicle on the side of the lithography mask comprises placing a pellicle comprising a copolymer of PVDF on the side of the lithography mask.
- 22. (New) The method of claim 21, wherein placing the pellicle comprises placing a pellicle comprising a block copolymer of PVDF on the side of the lithography mask.
- (New) The method of claim 21, wherein placing the 23. pellicle comprises placing a pellicle comprising a copolymer of PVDF and an amorphous fluoropolymer on the side of the lithography mask.

- (New) The method of claim 23, wherein placing the 24. pellicle comprises placing a pellicle comprising a copolymer of PVDF and a cyclic fluorocarbon oxygen-containing polymer on the side of the lithography mask.
- (New) The method of claim 23, wherein placing the 25. pellicle comprises placing a pellicle comprising a copolymer of PVDF and a polyimide linear fluoropolymer on the side of the lithography mask.
- (New) The method of claim 23, wherein placing the 26. pellicle comprises placing a pellicle comprising a copolymer of PVDF and a perfluorinated polyether on the side of the lithography mask.
- (New) The method of claim 23, wherein placing the 27. pellicle comprises placing a pellicle comprising a copolymer of PVDF and a combination of two or more of a cyclic fluorocarbon oxygen-containing polymer, a polyimide linear fluoropolymer, and a polyimide linear fluoropolymer on the side of the lithography mask.
- (New) The method of claim 20, wherein placing the 28. pellicle on the side of the lithography mask comprises placing a fluorinated pellicle on the side of the lithography mask.

- (New) The method of claim 20, wherein placing the 29. pellicle on the side of the lithography mask comprises placing a surface-modified pellicle on the side of the lithography mask.
- (New) The method of claim 20, wherein placing the 30. pellicle on the side of the lithography mask comprises stretching the pellicle over a frame above a surface of the mask.
- (New) The method of claim 20, wherein transmitting 31. the electromagnetic radiation comprises transmitting one or more of ultraviolet and far ultraviolet through the pellicle.
- (New) The method of claim 20, further comprising 32. spinning a solution that includes PVDF on a substrate.
- (New) The method of claim 20, further comprising 33. correcting for a change in transmissivity of the pellicle to the electromagnetic radiation.
- (New) The method of claim 33, wherein correcting for 34. the change in transmissivity of the pellicle comprises correcting for the change in transmissivity only after the pellicle has been exposed to more that about 12 J/cm2 of 157 nm wavelength radiation.

- 35. (New) The method of claim 33, wherein correcting for the change in transmissivity of the pellicle comprises correcting for the change in transmissivity only after the pellicle has been exposed to more that about 40 J/cm2 of 157 nm wavelength radiation.
- 36. (New) The method of claim 20, further comprising: stepping to a second position relative to the substrate; and

transmitting the electromagnetic radiation through the pellicle to form a second copy of the lithographic image on the substrate.